

## Guidelines for Abstract Preparation of ICPS2024 (Bold, 12 point, Times or Times New Roman)

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A **one-page abstract** should be prepared on a Letter-size page with 2 cm margins all around and **uploaded in the pdf format**. Templates are provided in L<sup>A</sup>T<sub>E</sub>X, Word and Open Document format. Authors who prefer a different typesetting system, please adhere to the following guidelines. Please do not change the style of the abstract (font types, sizes, spacings, margins, etc.). The submission deadline is **1 April 2024**.

The abstract must include the title of the paper, author(s), affiliation(s), address(es) and e-mail address of the corresponding author. In the title, capital letters should be used for the initial letter of each word except articles, prepositions and conjunctions. The main text should be typed single-spaced and at 11 point. The numbered list of all references should appear at the end of the abstract. When referring to them in the text, the reference number should be indicated by brackets, such as [1, 2]. Figures can be included; they should be numbered consecutively and accompanied by a figure caption in 10 point below the figure. Please do not generate page numbers.

When uploading your abstract you may indicate your preference for an oral or a poster presentation. Furthermore, please specify the tentative speaker/presenter and the category which is most appropriate for your contribution:

1. Material growth, structural properties and characterization, phonons.
2. Wide-bandgap semiconductors (GaN, SiC, Ga<sub>2</sub>O<sub>3</sub>, BN, Diamond).
3. Electron devices and applications: visible, MIR and THz.
4. Carbon: 2D graphene, 1D nanotubes, and 0D quantum dots.
5. 2D materials beyond graphene including twistrionics.
6. Perovskites/Organic semiconductors.
7. Topological states of matter, topological Insulators, and Weyl semimetals.
8. Low dimensional semiconductor systems (1D, 2D).
9. Quantum Hall effect, and fractional quantum Hall effect.
10. Spintronics and spin phenomena.
11. Optical properties, opto-electronics, solar cells.
12. Quantum optics, nano-photonics, quantum emitters, NV Centers.
13. Quantum technology: Semiconductor-based qubits.
14. Quantum technology: Quantum dots and nano-crystals.
15. Complex oxide and chalcogenide semiconductors.
16. Semiconductor-superconductor hybrid systems.
17. Nano-mechanics, MEMS/NEMS, and opto-mechanics.

### References

- [1] E. H. Hall, American Journal of Mathematics **2**, 287 (1879).
- [2] P. Debye and E. Hückel, Phys. Z. **24**, 185 (1923).



Fig. 1. ICPS2024 logo (caption 10 point, Times or Times New Roman)